

In the Claims:

Please amend claims 1-21 as indicated below. This listing of claims replaces all prior versions.

1. (Currently Amended) A field effect device (100), comprising:
a gate; a source; and at least one segmented field plate (111, 109), each of the at least one segmented field plates having a plurality of segments (115, 114) that each form a plate of a capacitor, wherein the field effect device (100) is connected to an electronic device (300) that dynamically selects first and second groups of segments of the plurality of segments in response to a selection signal and connects selected the first group of segments to the gate and the second group of segments to the source to selectively set a gate-to-drain (C_{GD})[[,]] and a drain-to-source (C_{DS}) capacitance.
2. (Currently Amended) A field effect device (100) as recited in claim 1, wherein the at least one segmented field plate further comprises a first segmented field plate (111) and a second segmented field plate (109).
3. (Currently Amended) A field effect device as recited in claim 1, wherein the field effect device (100) is a metal-oxide-semiconductor field effect transistor (MOSFET).
4. (Currently Amended) A field effect device (100) as recited in claim 2, wherein the second field plate (109) is at least partially disposed over the first field plate (111).
5. (Currently Amended) A field effect device (100) as recited in claim 4, wherein a dielectric layer (113) is disposed between the first (109) and the second segmented field plates (111) at a location where the second field plate partially overlaps the first field plate.
6. (Currently Amended) A field effect device (100) as recited in claim 3, wherein the field effect device is a semiconductor-on-insulator structure.

7. (Currently Amended) A field effect device (100) as recited in claim 1, wherein the field effect device is a semiconductor transistor, and the semiconductor is one of silicon, silicon-germanium or a III-V semiconductor material.
8. (Currently Amended) A field effect device (100) as recited in claim 1, wherein a ratio of the C_{GD} to the C_{DS} is ~~selectively and dynamically~~ controlled responsive to the selection signal ~~by the electronic device (300)~~.
9. (Currently Amended) A field effect device (100) as recited in claim 8, wherein the ratio is in the range of approximately 0.3 to approximately less than 0.9.
10. (Currently Amended) A field effect device (100) as recited in claim 1, wherein the field effect device is a component of an electrical switch.
11. (Currently Amended) An ultrasonic device (400), comprising:
a transducer (403) coupled to a switching device (401) that switches the transducer (403) between a transmit mode and a receive mode, wherein the switching device includes a field effect device (100) that includes a gate, a source and at least one segmented field plate (109, 111), each of the at least one segmented field plates having a plurality of segments (115, 114) that each form a plate of a capacitor, and wherein the field effect device is ~~connected to an electronic device (300) that dynamically~~ selects first and second groups of segments of the plurality of segments in response to a selection signal and connects selected the first group of segments to the gate and the second group of segments to the source to selectively set a gate-to-drain (C_{GD}) and a drain-to-source capacitance (C_{DS}).
12. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein the transducer (403) optimally operates at a particular ratio of C_{GD} to C_{DS} , and the ~~electronic device (300) connects the selected~~ first and second groups of segments are connected to the gate and the source to realize the particular ratio.

13. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein the ultrasonic device is adapted to connect to any of a plurality of transducers, each of which optimally operates at one of a particular ratio C_{GD} to C_{DS} , and the ~~electronic device connects said selected~~ first and second groups of segments are connected to the gate and the source to realize the particular ratio for one of said plurality of transducers when in use with the ultrasonic device.
14. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein the at least one segmented field plate (~~109, 111~~) further comprises a first segmented field plate and a second segmented field plate.
15. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein the field effect device (400) is a metal-oxide-semiconductor field effect transistor (MOSFET).
16. (Currently Amended) An ultrasonic device (400) as recited in claim 13, wherein the second segmented field plate (~~109~~) is at least partially disposed over the first field plate.
17. (Currently Amended) An ultrasonic device (400) as recited in claim 15, wherein a dielectric layer (~~113~~) is disposed between the first and the second segmented field plates (~~109, 111~~) at a location where the second field plate partially overlaps the first field plate.
18. (Currently Amended) An ultrasonic device (400) as recited in claim 14, wherein the field effect device (400) is a semiconductor-on-insulator structure.
19. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein the field effect device (400) is a semiconductor transistor, and the semiconductor is one of silicon, silicon-germanium or a III-V semiconductor material.
20. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein ~~the electronic device (300) includes a multiplexer (304), which receives~~ the first and second

groups of segments are selected based on an input from the transducer, ~~and based on the~~
~~input effects the dynamic selection.~~

21. (Currently Amended) An ultrasonic device (400) as recited in claim 11, wherein the
 C_{GD} is less than the C_{DS} .